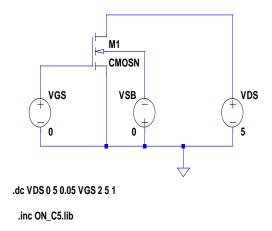
ECE 531 Microelectronics Assignment 3

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Problem 1:



 $\label{eq:figure 1} Figure \ 1: LTS pice \ circuit \ diagram \ of \ NMOS \ transistor \ using \ CMOSN \ model.$

Here W/L = $7.2 \mu m / 0.6 \mu m$

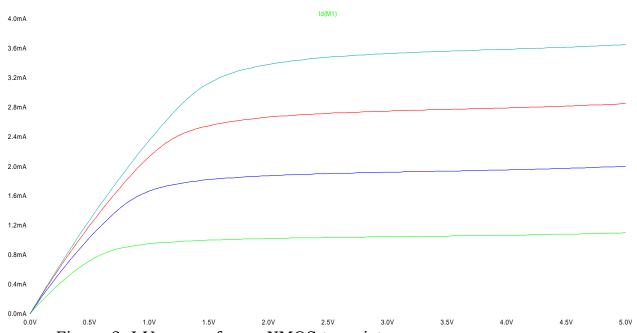


Figure 2: I-V curves for an NMOS transistor

```
SPICE Netlist: E:\Jan_2015\Microelectronic systems\Assignment_3\circuits\prob_1.net
* E:\Jan_2015\Microelectronic systems\Assignment_3\circuits\prob_1.asc
VGS N003 0 0
VDS N001 0 5
VSB 0 N002 0
M1 N001 N003 0 N002 CMOSN 1=0.6u w=7.2u
.model NMOS NMOS
.model PMOS PMOS
.lib D:\LTSpice\lib\cmp\standard.mos
.dc VDS 0 5 0.05 VGS 2 5 1
.inc ON C5.lib
.backanno
.end
```

Figure 3: Spice Netlist

Problem 2:

NMOS transistor in series:

Here width W= 3 μm ; L = 0.6 μm

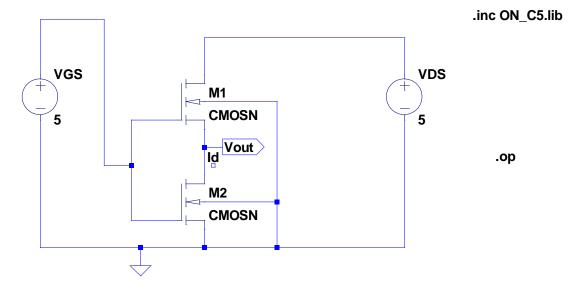


Figure 4: NMOS transistors in series

Figure 5: Operating point for NMOS transistors in series

Voltage V(out) = 1.135 Volts. Current $I_d = 0.000941$ amps = 941 μA

Problem 3:

Given W = 8
$$\lambda$$
 = 8*0.3 μ m = 2.4 μ m
L = 2 λ = 2*0.3 μ m = 0.6 μ m
VDD = 5 V

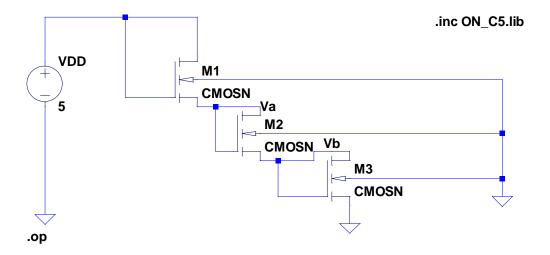


Figure 6: LTSpice figure of the required transistor circuit

```
SPICE Netlist: E:\Jan_2015\Microelectronic systems\Assignment_3\circuits\prob_3.net

* E:\Jan_2015\Microelectronic systems\Assignment_3\circuits\prob_3.asc
M1 N001 N001 Va 0 CMOSN 1=0.6u w=2.4u
M2 Va Va Vb 0 CMOSN 1=0.6u w=2.4u
VDD N001 0 5
.model NMOS NMOS
.model PMOS PMOS
.lib D:\LTSpice\lib\cmp\standard.mos
.op
.inc ON_C5.lib
.backanno
.end
```

Figure 7: Spcie Netlist of the required transistor circuit

∡ * E:\	Jan_2015\Microeled	ctronic systems\Assignment_3\circuits\prob_3.asc	×
Op	erating Point	-	
V(n001):	5	voltage	
V(va):	3.23171	voltage	
V(vb):	1.52802	voltage	
Id(M3):	0.000152926	device_current	
Ig(M3):	0	device_current	
Ib(M3):	-1.53802e-012	device current	
Is(M3):	-0.000152926	device_current	
Id(M2):	0.000152926	device current	
Ig(M2):	0	device current	
Ib(M2):	-4.77973e-012	device current	
Is(M2):	-0.000152926	device current	
Id(M1):	0.000152926	device current	
Ig(M1):	0	device current	
Ib(M1):	-8.25171e-012	device current	
Is(M1):	-0.000152926	device current	
I(Vdd):		device current	
		_	

From the spcie operating point figure

$$V_a = 3.23 V$$
; $V_b = 1.52 V$;

And the currents Id, Is, Ig and Ib are obtained.

Problem 4:

a. To find the threshold voltage if $V_{sb}=3V$

$$V_T = V_{T0} + \gamma (\sqrt{|-2\emptyset_F + V_{SB}|} - \sqrt{|-2\emptyset_F|})$$

From the given values

$$V_T = 0.8 + 0.6(\sqrt{2.4} - \sqrt{0.6})$$
$$= 0.8 + 0.6^* \cdot 0.775$$

$$V_T = 1.265 V$$

b. To convert C_{J0} to units fF/ μm^2

Here f = $10^{-15} \mu = 10^{-6}$

$$= 4 * 10^{-4} * \frac{10^{-15}}{10^{-15}} * \frac{10^{-6}}{10^{-6}} \frac{F}{m^2}$$
$$= 4 * 10^5 \frac{fF}{\mu m^2}$$

c. To find bottom capacitance. Given $V_{sb}=3V$; AS=50p We have $C_j=\frac{C_{j0}}{(1-\frac{V_D}{\emptyset_0})^m}$

$$C_j = \frac{4 * 10^{-4}}{(1 - (\frac{-3}{0.74})^{0.43})}$$

$$C_j = 1.992 * 10^{-4} \frac{F}{m^2}$$

Bottom capacitance $C_{bottom} = C_J * Area$

=
$$1.992 * 10^{-4} * 50 * 10^{-12}$$

= $99.6 * 10^{-16}$

Bottom capacitance=9.96 fF

Problem 5:

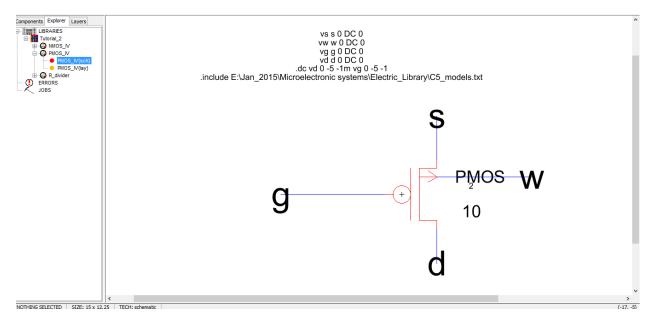


Figure 8: Schematic view of PMOS Transistor

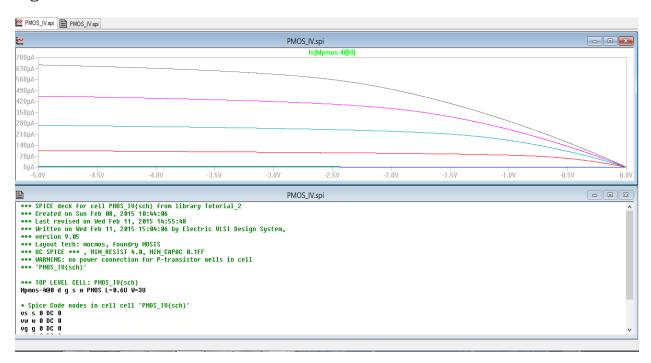


Figure 9 : Spice simulation view of PMOS transistor

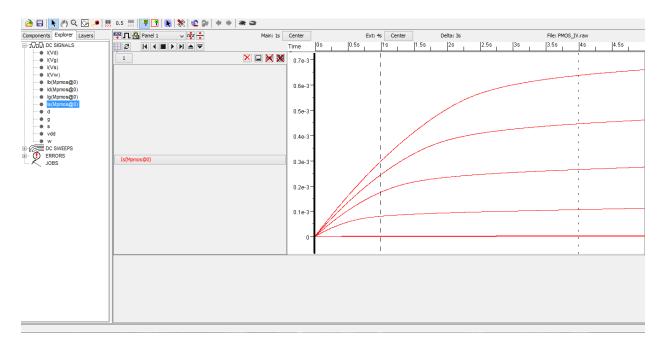


Figure 10: Electric simulation of PMOS transistor

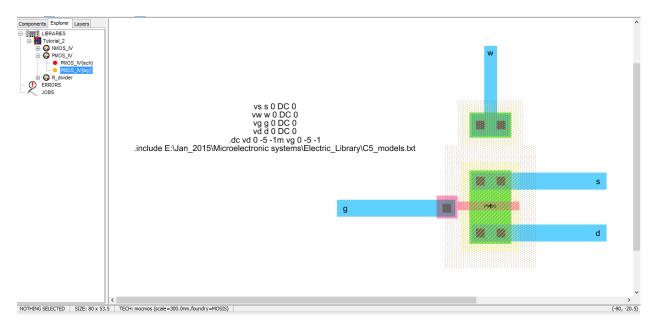


Figure 11: Layout view of PMOS transistor

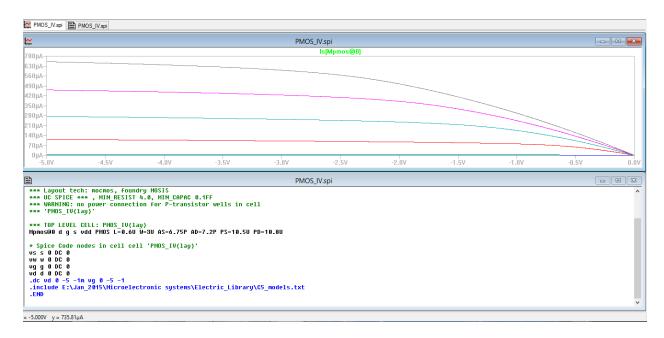


Figure 12: Spice simulation output of PMOS transistor

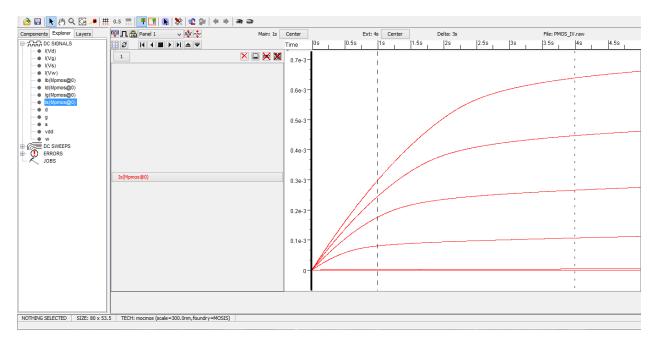


Figure 13: Electric simulation output of PMOS transistor

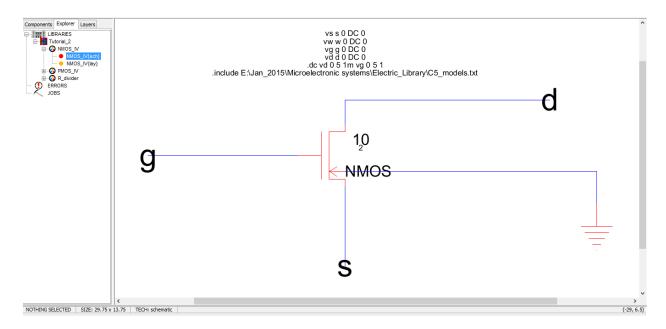


Figure 14: Schematic view of NMOS transistor

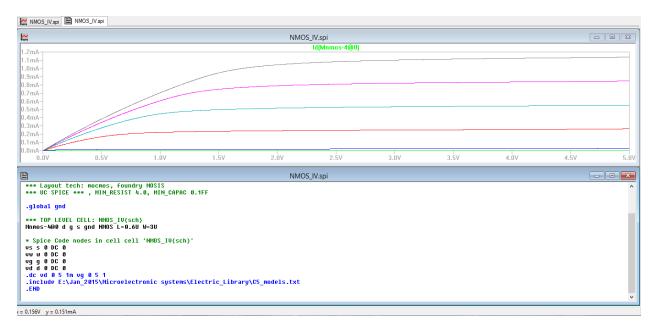


Figure 15: Spice simulation result of NMOS transistor

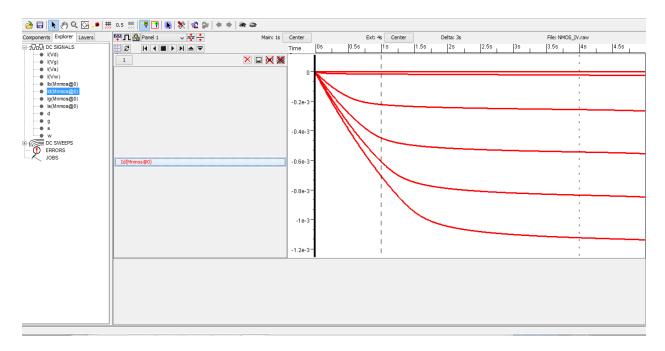


Figure 16: Electric simulation of NMOS transistor

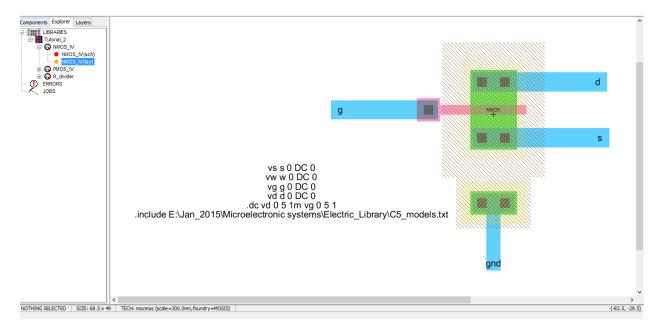


Figure 17: Layout view of NMOS transistor



Figure 18: Spice simulation output of NMOS transistor

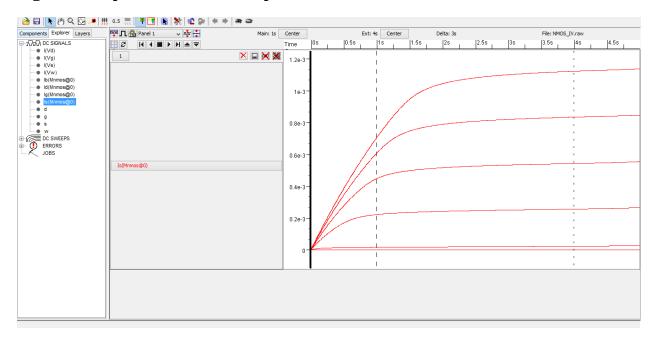


Figure 19: Electric simulation of NMOS transistor